ABSTRACT OF THE DISCLOSURE

A method of fabricating a compound semiconductor device having an ohmic electrode of a low contact potential and an apparatus for fabricating a compound semiconductor device are obtained. The method comprises a substrate cleaning step including a first cleaning step of heating a compound semiconductor substrate (1) containing a first conductivity type impurity in a temperature range of not more than 250°C for etching its surface with hydrogen chloride and a second cleaning step of performing a radical hydrotreatment on the compound semiconductor substrate etched with hydrogen chloride after the first cleaning step.

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